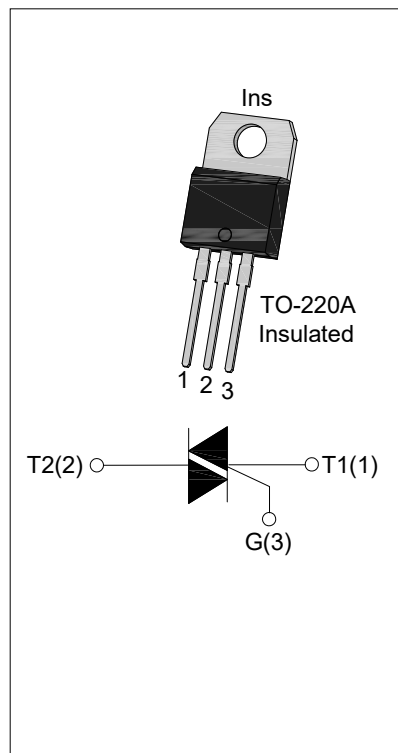




### DESCRIPTION:

With high ability to withstand the shock loading of large current, JST20A-800BW triacs provide high dv/dt rate with strong resistance to electromagnetic interface. With high commutation performances, especially recommended for use on inductive load. From all three terminals to external heatsink, JST20A -800BW provide a rated insulation voltage of 2500  $V_{RMS}$ , complying with UL standards (File ref: E252906). Packages TO-220A is RoHS compliant. (2011/65/EU)



### MAIN FEATURES

Symbol	Value	Unit
$I_{T(RMS)}$	20	A
$V_{DRM} / V_{RRM}$	800	V

### ABSOLUTE MAXIMUM RATINGS

Parameter		Symbol	Value	Unit
Storage junction temperature range		$T_{stg}$	-40-150	°C
Operating junction temperature range		$T_j$	-40-125	°C
Repetitive peak off-state voltage ( $T_j=25^\circ\text{C}$ )		$V_{DRM}$	800	V
Repetitive peak reverse voltage ( $T_j=25^\circ\text{C}$ )		$V_{RRM}$	800	V
Non repetitive surge peak Off-state voltage		$V_{DSM}$	$V_{DRM} + 100$	V
Non repetitive peak reverse voltage		$V_{RSM}$	$V_{RRM} + 100$	V
RMS on-state current	TO-220A(Ins) ( $T_C=70^\circ\text{C}$ )	$I_{T(RMS)}$	20	A
Non repetitive surge peak on-state current (full cycle, F=50Hz)		$I_{TSM}$	200	A
$I^2t$ value for fusing ( $t_p=10\text{ms}$ )		$I^2t$	200	$\text{A}^2\text{s}$
Critical rate of rise of on-state current ( $I_G=2 \times I_{GT}$ )		$di/dt$	50	$\text{A}/\mu\text{s}$

Peak gate current	$I_{GM}$	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W
Peak gate power	$P_{GM}$	10	W

**ELECTRICAL CHARACTERISTICS** ( $T_j=25^{\circ}C$  unless otherwise specified)

Symbol	Test Condition	Quadrant		Value	Unit
$I_{GT}$	$V_D=12V R_L=33\Omega$	I - II -III	MAX	50	mA
$V_{GT}$		I - II -III	MAX	1.3	V
$V_{GD}$	$V_D=V_{DRM} T_j=125^{\circ}C$ $R_L=3.3K\Omega$	I - II -III	MIN	0.2	V
$I_L$	$I_G=1.2I_{GT}$	I -III	MAX	70	mA
		II		90	
$I_H$	$I_T=100mA$		MAX	60	mA
dv/dt	$V_D=2/3V_{DRM}$ Gate Open $T_j=125^{\circ}C$		MIN	1000	V/ $\mu s$

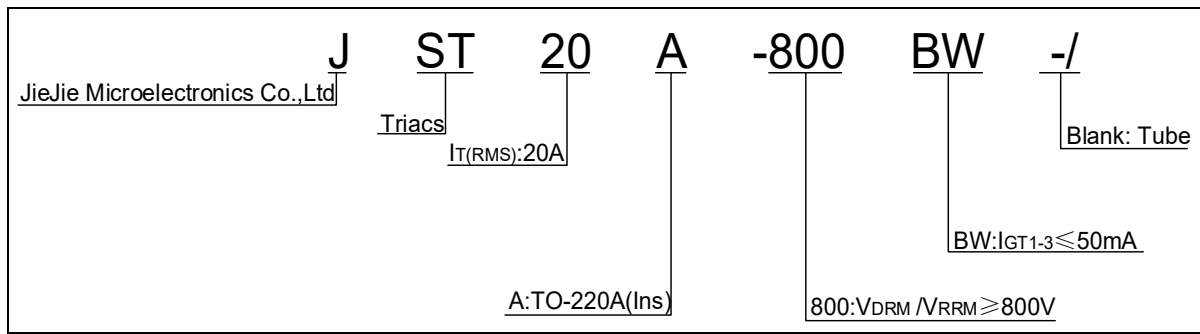
**STATIC CHARACTERISTICS**

Symbol	Parameter		Value(MAX)	Unit
$V_{TM}$	$I_{TM}=28A t_p=380\mu s$	$T_j=25^{\circ}C$	1.5	V
$V_{TO}$	Threshold voltage	$T_j=125^{\circ}C$	0.88	V
$R_d$	Dynamic resistance	$T_j=125^{\circ}C$	14.72	m $\Omega$
$I_{DRM}$	$V_D=V_{DRM} V_R=V_{RRM}$	$T_j=25^{\circ}C$	5	$\mu A$
$I_{RRM}$		$T_j=125^{\circ}C$	2.5	mA

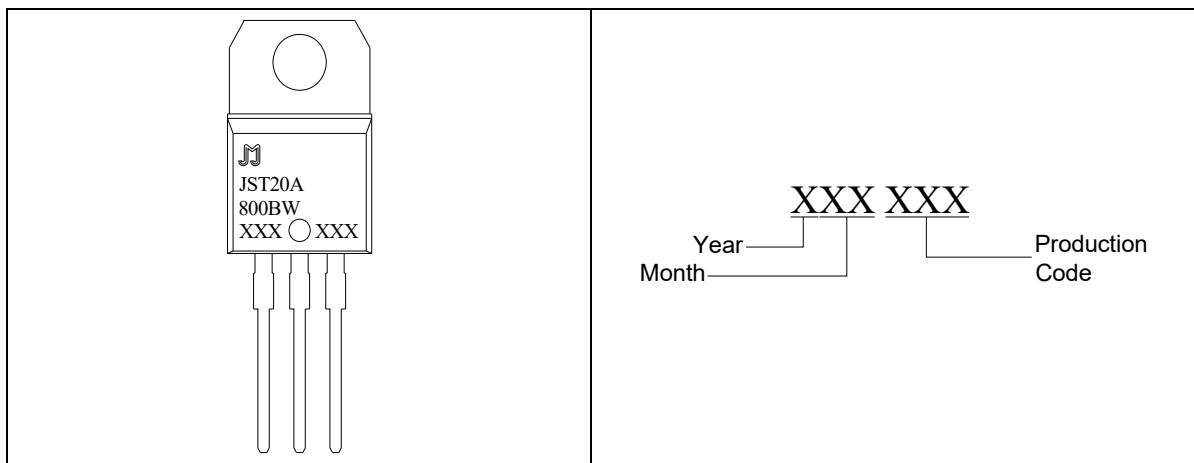
**THERMAL RESISTANCES**

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	junction to case(AC)	TO-220A(Ins)	2.2	$^{\circ}C/W$

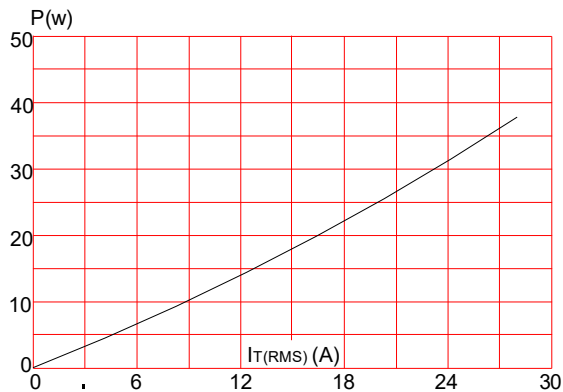
**ORDERING INFORMATION**



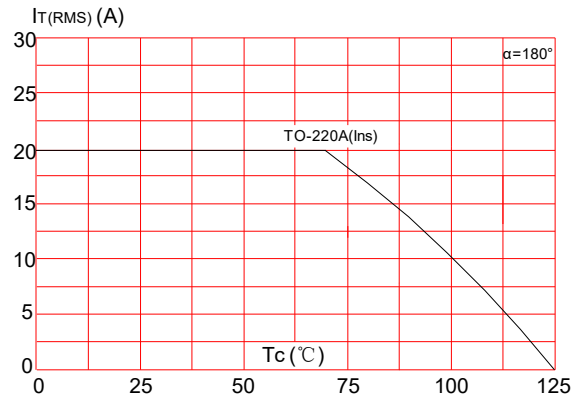
**MARKING**



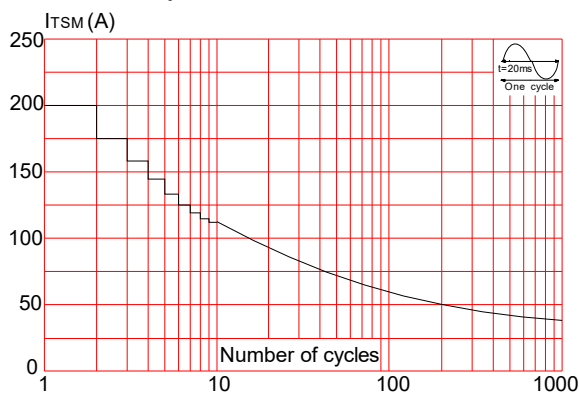
**FIG.1** Maximum power dissipation versus RMS on-state current



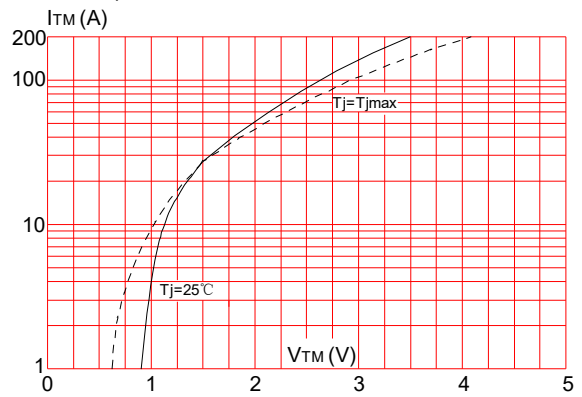
**FIG.2:** RMS on-state current versus case temperature



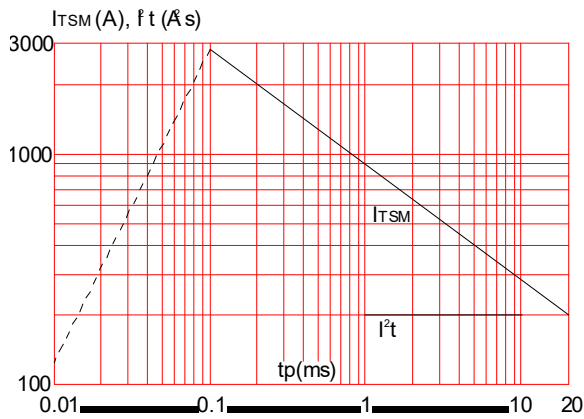
**FIG.3:** Surge peak on-state current versus number of cycles



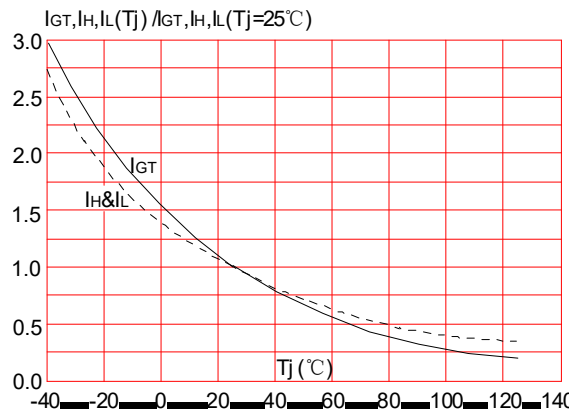
**FIG.4:** On-state characteristics (maximum values)



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 20\text{ms}$ , and corresponding value of  $\int I^2 t (dI/dt < 50\text{A}/\mu\text{s})$



**FIG.6:** Relative variations of gate trigger current holding current and latching current versus junction temperature



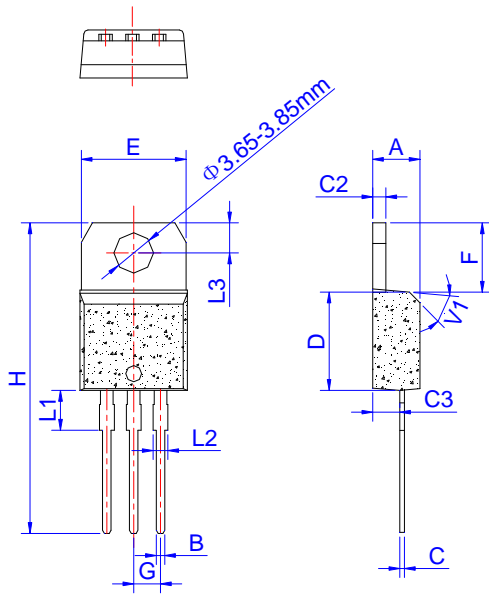
**ORDERING INFORMATION**

Order code	Voltage $V_{DRM}/V_{RRM}$ (V)	IGT(mA)	Package	Base qty. (pcs)	Delivery mode
JST20A-800BW	800	50	TO-220A(Ins)	50	Tube

**Document Revision History**

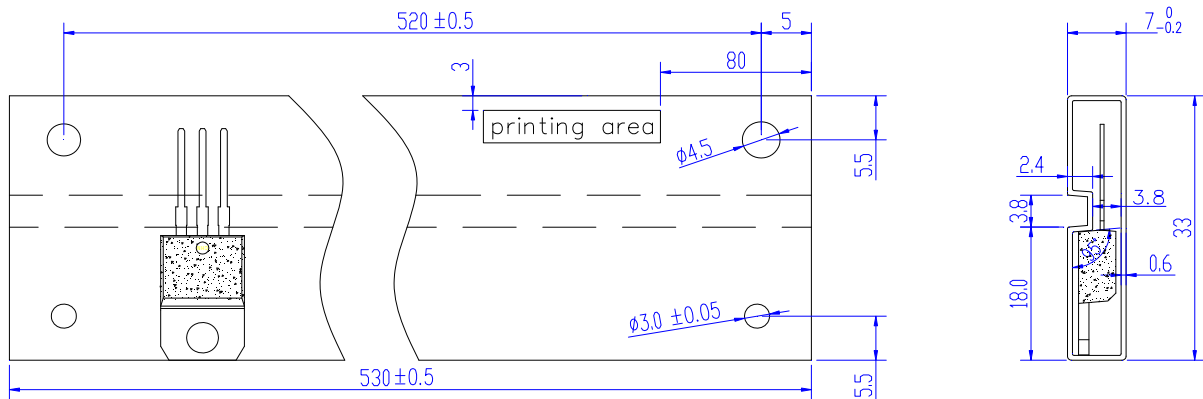
Date	Revision	Changes
Mar 27, 2022	1	Last update

PACKAGE MECHANICAL DATA



Ref.	Dimensions					
	Millimeters			Inches		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.40		4.60	0.173		0.181
B	0.61		0.88	0.024		0.035
C	0.46		0.70	0.018		0.028
C2	1.21		1.32	0.048		0.052
C3	2.40		2.72	0.094		0.107
D	8.60		9.70	0.339		0.382
E	9.80		10.4	0.386		0.409
F	6.55		6.95	0.258		0.274
G	2.40		2.70	0.094		0.106
H	28.0		29.8	1.102		1.173
L1		3.75			0.148	
L2	1.14		1.70	0.045		0.067
L3	2.65		2.95	0.104		0.116
V1		45°			45°	


DELIVERY MODE



PACKAGE	OUTLINE	TUBE (PCS)	INNER BOX (PCS)	PER CARTON
TO-220A	TUBE	50	1,000	5,000



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